L Number	Hits	Search Text	DB	Time stamp
8	2207	((427/240) or (118/52) or (427/425) or (118/320)).CCLS.	USPAT; US-PGPUB	2004/05/23 20:58
9	61	(((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)	USPAT; US-PGPUB	2004/05/23 21:05
10	27	((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320	USPAT; US-PGPUB	2004/05/23 20:59
11	8	(((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3	USPAT; US-PGPUB	2004/05/23 20:59
12	921	semiconductor and wafer and (heat$3 same inert) and oxidiz$3 and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)	USPAT; US-PGPUB	2004/05/23 21:05
13	237	semiconductor and wafer and ((heat$3 same inert) same oxidiz$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)	USPAT; US-PGPUB	2004/05/23 21:24
14	51	semiconductor and wafer.ab. and ((heat$3 same inert) same oxidiz$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)	USPAT; US-PGPUB	2004/05/23 21:24
15	3	semiconductor and wafer.ab. and ((heat$3 same inert) same oxidiz$3).ab. and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)	USPAT; US-PGPUB	2004/05/23 21:06
16	16	(semiconductor and wafer.ab. and ((heat$3 same inert) same oxidiz$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)) and (coat$3 same heat$3)	USPAT; US-PGPUB	2004/05/23 21:07
17	29	semiconductor and wafer and ((heat$3 same inert) same oxidiz$3 same coat$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)	USPAT; US-PGPUB	2004/05/23 21:24
18	21	(semiconductor and wafer and ((heat$3 same inert) same oxidiz$3 same coat$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)) not ((semiconductor and wafer.ab. and ((heat$3 same inert) same oxidiz$3) and @ad<19980320 not ((((((427/240) or (118/52) or (427/425) or (118/320)).CCLS.) and wafer and (heat$3 same inert)) and @ad<19980320) and oxidiz$3)) and (coat$3 same heat$3))	USPAT; US-PGPUB	2004/05/23 21:42
20	276	(semiconductor adj wafer) and (((hot or heat or heating) adj plate) same pin)	USPAT; US-PGPUB	2004/05/23 21:44
21	99	(semiconductor adj wafer) and (((hot or heat or heating) adj plate) same pin) and inert	USPAT; US-PGPUB	2004/05/23 21:56
22	14	((semiconductor adj wafer) and (((hot or heat or heating) adj plate) same pin) and inert) and @ad<19980320	USPAT; US-PGPUB	2004/05/23 21:44
23	0	(wafer) and (((hot or heat or heating) adj plate) same pin) and inert and @ad<19980320 not (((semiconductor adj wafer) and (((hot or heat or heating) adj plate) same pin) and inert) and @ad<19980320)	USPAT; US-PGPUB	2004/05/23 21:56